



PTO/SB/08A (10-01)
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Substitute for form 1449A/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	09/954,864	
			Filing Date	9/17/01	
			First Named Inventor	Patel	
			Art Unit	1763	
			Examiner Name	Olsen, Allan	
Sheet	1	of	6	Attorney Docket Number	P68-US

U.S. PATENT DOCUMENTS					
Examiner Initials ²	Cite No. ¹	Document Number Number - Kind Code ³ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
Awo		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
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Awo		EP-0704884-A2	04-03-1996	Mehta, J.		
		EP-0822582-A2	02-04-1998	Bhardwai, J.K.		
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Examiner Signature	<i>Allan Olsen</i>	Date Considered	3/7/05
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			Application Number	09/954.864
Sheet 2 of 6			Filing Date	9/17/01
			First Named Inventor	Patel
			Art Unit	1763
			Examiner Name	Olsen, Allan
			Attorney Docket Number	P68-US

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		Number - Kind Code ² (if known)			
Auo		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
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Auo		JP-1997/09251981-A	09-22-1997	Kazuaki et al.		
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		JP-1986/61181131-A	08-13-1986	Shinji et al.		

Examiner Signature	<i>Allan Olsen</i>	Date Considered	3-7-05
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet 3 of 6

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		Country Code ³ -Number ⁴ - Kind Code ⁵ (if known)				
<i>Ago</i>		JP-1989/01208834-A	08-22-1989	Nobuo et al.		
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Complete If Known	
		Application Number	09/954,864
		Filing Date	9/17/01
		First Named Inventor	Patel
		Group Art Unit	1763
		Examiner Name	Olsen, Allan
		Attorney Docket Number	P68-US
Sheet	4	of	6

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
Auo		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F2 and XeF2 Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
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Auo		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF ₂ Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
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